

JST137F-800F 8A TRIAC

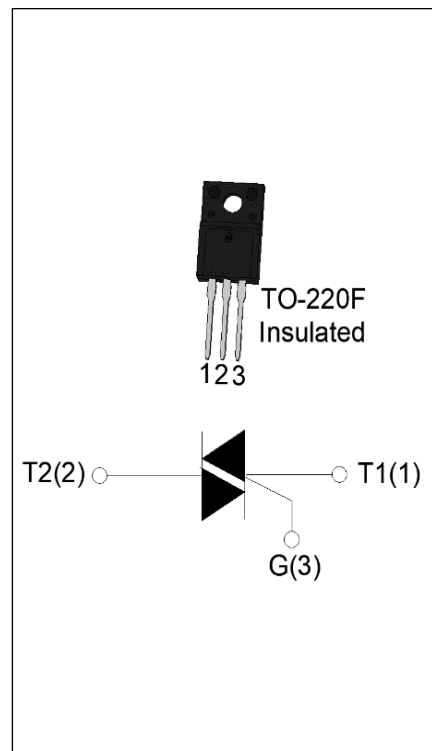
Rev.A.1.1

DESCRIPTION:

The JST137F-800F triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. By using an external plastic package, JST137F-800F provides a rated insulation voltage of 2000 VRMS, complying with UL standards (File ref: E252906). Package TO-220F is RoHS compliant.

MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	8	A
V_{DRM}/V_{RRM}	800	V
$I_{GT\ I/II/III/IV}$	25/25/25/70	mA


ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		T _{stg}	-40-150	℃
Operating junction temperature range		T _j	-40-125	℃
Repetitive peak off-state voltage (T _j =25℃)		V _{DRM}	800	V
Repetitive peak reverse voltage (T _j =25℃)		V _{RRM}	800	V
RMS on-state current (T _C ≤74℃)		I _{T(RMS)}	8	A
Non repetitive surge peak on-state current (full cycle , t _p =20ms , T _j =25℃)		I _{TSM}	65	A
Non repetitive surge peak on-state current (full cycle , t _p =16.6ms , T _j =25℃)			72	
I ² t value for fusing (t _p =10ms , T _j =25℃)		I ² t	21	A ² s
Critical rate of rise of on-state current (I _G =2×I _{GT} , f=100Hz , T _j =125℃)	I - II -III	di/dt	100	A/μs
	IV		50	
Peak gate current (t _p =20μs , T _j =125℃)		I _{GM}	4	A
Average gate power dissipation (T _j =125℃)		P _{G(AV)}	0.5	W
Peak gate power		P _{GM}	10	W

Peak pulse voltage ($T_j=25^{\circ}\text{C}$; non-repetitive, off-state; FIG.7)	V_{pp}	4	kV
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ELECTRICAL CHARACTERISTICS ($T_j=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12\text{V}$ $R_L=33\Omega$	I - II - III	MAX.	25	mA
		IV		70	
V_{GT}		ALL	MAX.	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125^{\circ}\text{C}$ $R_L=3.3\text{k}\Omega$	ALL	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	I - III - IV	MAX.	50	mA
		II		80	
I_H	$I_T=500\text{mA}$		MAX.	40	mA
dV/dt	$V_D=540\text{V}$ Gate Open $T_j=125^{\circ}\text{C}$		MIN.	300	$\text{V}/\mu\text{s}$
$(dV/dt)_c$	$(dI/dt)_c=2.7\text{A/ms}$, $T_j=125^{\circ}\text{C}$		MIN.	8	$\text{V}/\mu\text{s}$
t_{on}	$I_G=80\text{mA}$ $I_A=400\text{mA}$ $I_R=40\text{mA}$ $T_j=25^{\circ}\text{C}$		TYP.	5	μs
t_{off}				50	

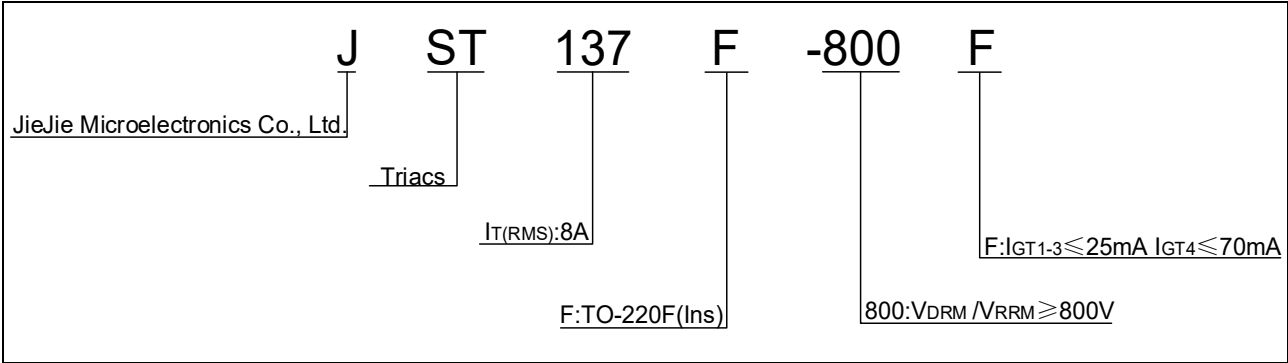
STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=10\text{A}$ $t_p=380\mu\text{s}$	$T_j=25^{\circ}\text{C}$	1.5	V
V_{TO}	Threshold voltage	$T_j=125^{\circ}\text{C}$	0.8	V
R_D	Dynamic resistance	$T_j=125^{\circ}\text{C}$	53	$\text{m}\Omega$
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25^{\circ}\text{C}$	5	μA
I_{RRM}		$T_j=125^{\circ}\text{C}$	0.45	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	4.5	$^{\circ}\text{C}/\text{W}$
$R_{th(j-a)}$	junction to ambient (AC)	60	$^{\circ}\text{C}/\text{W}$

ORDERING INFORMATION



MARKING

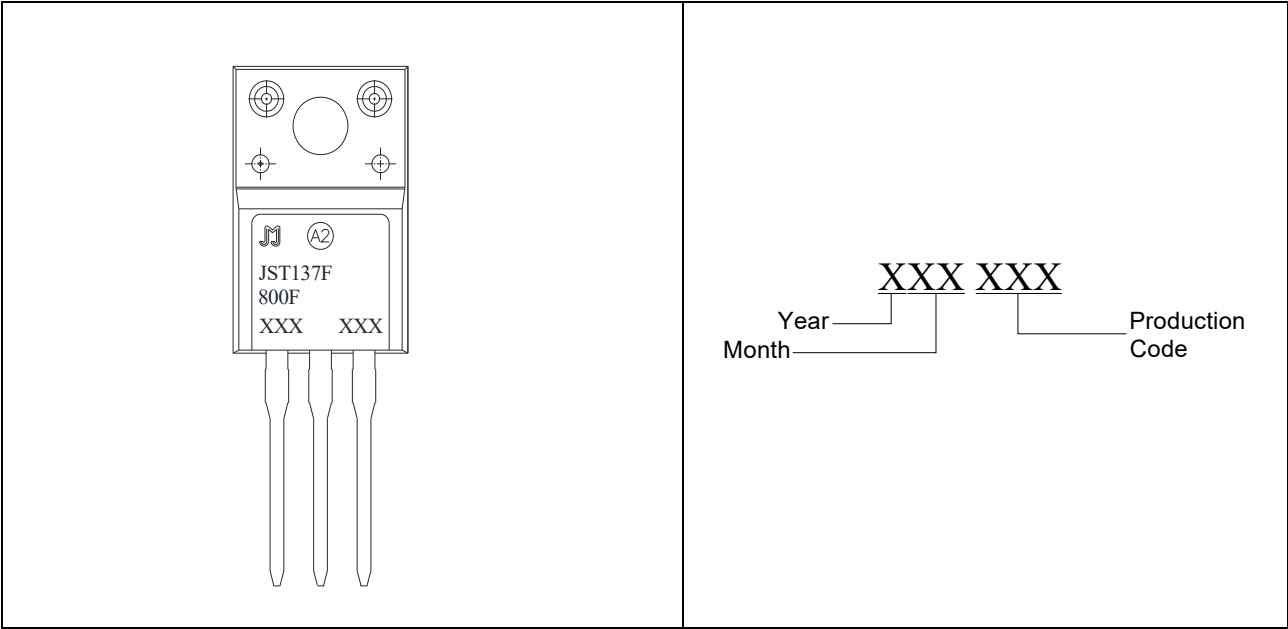


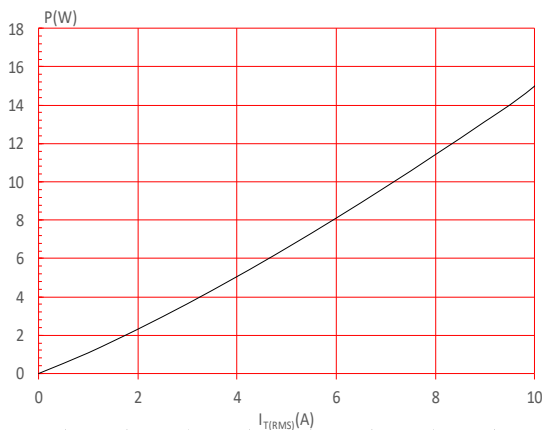
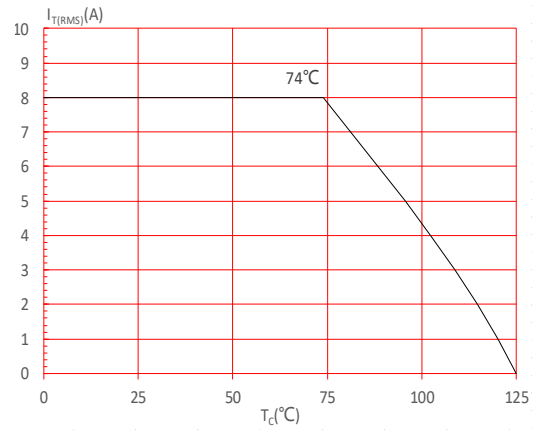
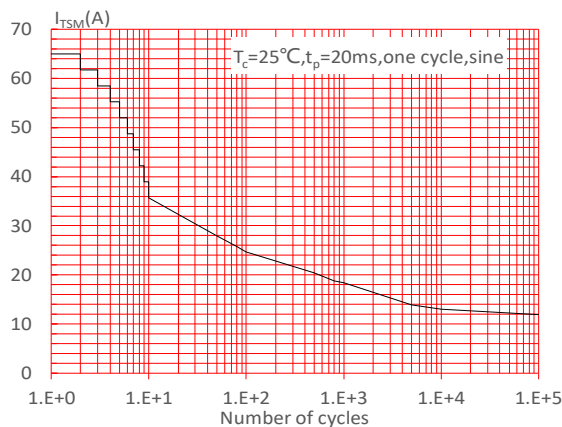
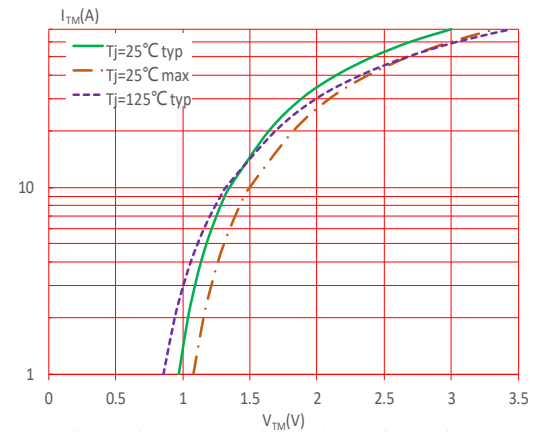
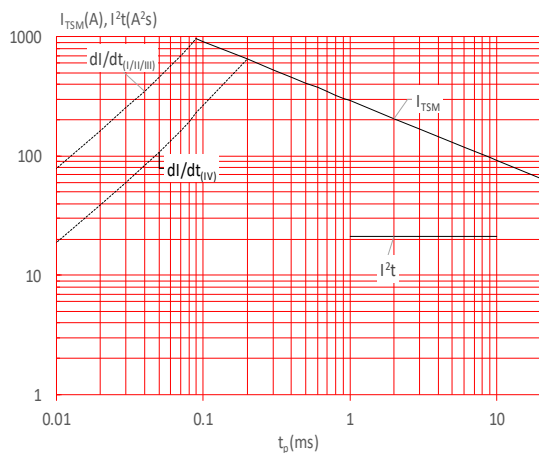
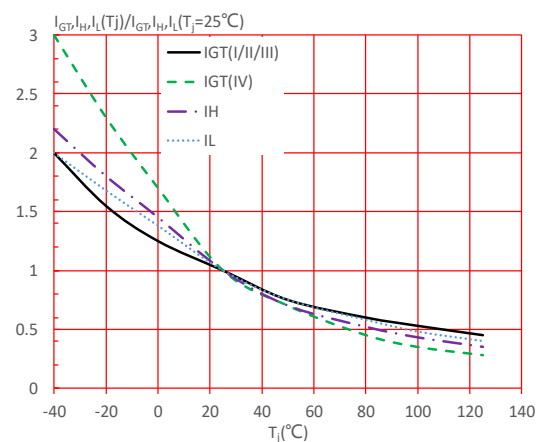
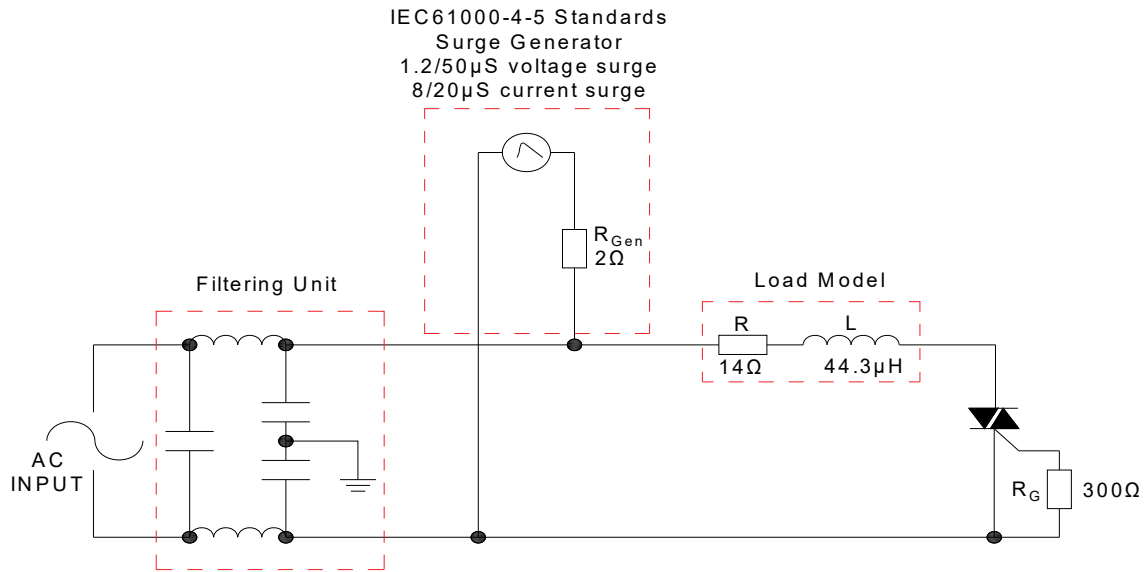
FIG.1: Maximum power dissipation versus RMS on-state current**FIG.2:** RMS on-state current versus case temperature**FIG.3:** Surge peak on-state current versus number of cycles**FIG.4:** On-state characteristics**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20ms$, and corresponding value of I^2t (I - II - III: $dl/dt < 100A/\mu s$; IV: $dl/dt < 50A/\mu s$)**FIG.6:** Relative variations of gate trigger current, holding current and latching current versus junction temperature

FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards

LEAD FORMING AND SOLDERING

Refer to the application note “Assembly Instructions for Thyristors in Through-hole Package” released by JieJie Microelectronics.

ORDERING INFORMATION

Order code	Voltage $V_{\text{DRM}}/V_{\text{RRM}}$ (V)	IGT(mA)		Package	Base qty. (pcs)	Delivery mode
		I - II - III	IV			
JST137F-800F	800	25	70	TO-220F(Ins)	50	Tube

Document Revision History

Date	Revision	Changes
Apr.14, 2023	A.1.0	Last updated
Oct.15, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA

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